E1

comprising a boron phosphide (BP)-based material on a front surface of said single crystal substrate, a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure on said buffer layer, and a window layer comprising an

D1

electrically conducting transparent oxide crystal layer on said group-III nitride crystal layer, wherein at least a second conduction-type surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer, a pad electrode for wire bonding is disposed on the center of the upper surface of said window layer, said second conduction-type surface ohmic electrode is composed of a plurality of electrodes and does not exist below said pad electrode, and said window layer covers the surface of said group-III nitride crystal layer below said pad electrode.

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11. (Three Times Amended) An electrode for group-III nitride semiconductor light-emitting diodes for a group-III nitride semiconductor light-emitting diode comprising at least a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of a hetero-junction structure, and a window layer comprising an electrically conducting transparent

D2

oxide crystal layer provided on said group-III nitride crystal layer, wherein at least a surface ohmic electrode conductive with said window layer is between the surface of said group-III nitride crystal layer and said window layer and comes into contact with the surface of said group-III nitride crystal layer, a pad electrode for wire bonding is disposed on the center of the upper surface of said window layer, said surface ohmic electrode is composed of a plurality of

electrodes and does not exist below said pad electrode, and said window layer covers the surface of said group-III nitride crystal layer below said pad electrode.

19. (Three Times Amended) A method for producing an electrode for group-III nitride semiconductor light-emitting diodes, comprising

forming a plurality of surface ohmic electrodes in contact with a surface of a gallium nitride (GaN)-based group-III nitride crystal layer having a light-emitting part of hetero-junction structure,

then covering the surface of said group-III nitride crystal layer and said surface ohmic electrodes to form a window layer comprising an electrically conducting transparent oxide crystal layer conductive with said surface ohmic electrodes, and

then forming a pad electrode for wire bonding on a center of the upper surface of said window layer conductive with said window layer, wherein said surface ohmic electrodes do not exist below said pad electrode, and said window layer covers the surface of said group-III nitride crystal layer below said pad electrode.